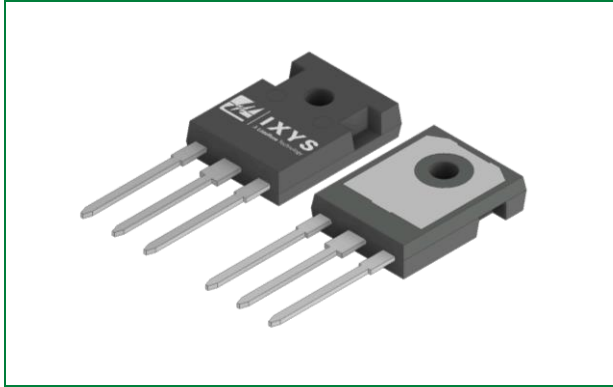


LSIC1MO170E0750 1700 V, 750 mOhm N-Channel SiC MOSFET

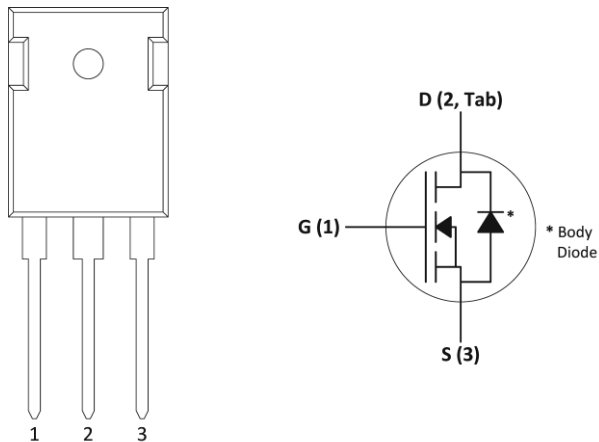


Agency Approvals and Environmental

Environmental Approvals



Circuit Diagram



Product Summary

Characteristic	Value	Unit
V_{DS}	1700	V
Typical $R_{DS(ON)}$	750	mOhm
I_D ($T_C \leq 100^\circ\text{C}$)	4.4	A

Features

- Optimized for high-frequency, high-efficiency applications
- Extremely low gate charge and output capacitance
- Low gate resistance for high-frequency switching
- Normally-off operations at all temperatures
- Ultra-low on-resistance

Applications

- High-frequency applications
- Solar Inverters
- Switch Mode Power Supplies
- UPS
- Motor Drives
- High Voltage DC/DC Converters
- Battery Chargers
- Induction Heating

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1. Maximum Ratings

Characteristic	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}	$V_{GS} = 0\text{ V}$	1700	V
Continuous Drain Current	I_D	$V_{GS} = 20\text{ V}, T_C = 25\text{ }^\circ\text{C}$	6.2	A
		$V_{GS} = 20\text{ V}, T_C = 100\text{ }^\circ\text{C}$	4.4	
Pulsed Drain Current ¹	$I_{D(pulse)}$	$T_C = 25\text{ }^\circ\text{C}$	11	A
Power Dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}, T_J = 175\text{ }^\circ\text{C}$	60	W
Gate-Source Voltage	$V_{GS,MAX}$	Absolute maximum values – Steady state	–6 to +22	V
	$V_{GS,OP,TR}$ ²	Transient, $t_{transient} < 300\text{ nsec}$	–10 to +25	
	$V_{GS,OP}$ ³	Recommended DC operating values	–5 to +20	
Operating Junction Temperature	T_J	-	–55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}	-	–55 to +150	$^\circ\text{C}$
Lead Temperature for Soldering	T_{SOLD}	-	260	$^\circ\text{C}$
Mounting Torque	M_D	M3 or 6-32 screw	1	Nm
			8.8	in-lb

Footnote 1: Pulse width limited by $T_{J,MAX}$

Footnote 2: See Figure 21 for further information

Footnote 3: MOSFET can operate with $V_{GS(OFF)} = 0\text{ V}$ – dependent upon PCB layout. $V_{GS(OFF)} = -5\text{ V}$ provides added noise margin and faster turn-off speed

2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Typical Thermal Resistance, junction-to-case	$R_{th,JC,MAX}$	2.5	$^\circ\text{C/W}$
Maximum Thermal Resistance, junction-to-ambient	$R_{th,JA,MAX}$	40	$^\circ\text{C/W}$

3. Electrical Characteristics

3.1. Static Characteristics ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	1700	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 1700\text{ V}, V_{GS} = 0\text{ V}$	-	0.05	10	μA
		$V_{DS} = 1700\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	0.1	-	
Gate Leakage Current	$I_{GSS,F}$	$V_{GS} = 22\text{ V}, V_{DS} = 0\text{ V}$	-	-	100	nA
	$I_{GSS,R}$	$V_{GS} = -6\text{ V}, V_{DS} = 0\text{ V}$	-	-	100	
Drain-Source On-State Resistance	$R_{DS(ON)}$	$I_D = 2\text{ A}, V_{GS} = 20\text{ V}$	-	750	1000	m Ω
		$I_D = 2\text{ A}, V_{GS} = 20\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	1550	-	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1.8	2.8	4.0	V
		$V_{DS} = V_{GS}, I_D = 1\text{ mA}, T_J = 175\text{ }^\circ\text{C}$	-	1.9	-	
Gate Resistance	R_G	Resonance method, Drain-Source shorted ¹	-	29	-	Ω

Footnote 1: For a description of the resonance method for measuring R_G , refer to the JEDEC Standard JESD24-11 test method

3.2. Dynamic Characteristics ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Turn-On Switching Energy	E_{ON}	$V_{DD} = 1200\text{ V}$, $I_D = 2\text{ A}$, $V_{GS} = -5 / +20\text{ V}$, $R_{G,ext} = 2\text{ }\Omega$, $L = 1.4\text{ mH}$, FWD = LSIC1MO170E0750	-	52	-	μJ
Turn-Off Switching Energy	E_{OFF}		-	61	-	
Total Per-Cycle Switching Energy	E_{TS}		-	113	-	
Input Capacitance	C_{ISS}	$V_{DD} = 1000\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$, $V_{AC} = 25\text{ mV}$	-	200	-	pF
Output Capacitance	C_{OSS}		-	11.5	-	
Reverse Transfer Capacitance	C_{RSS}		-	1.7	-	
COSS Stored Energy	E_{OSS}		-	5.7	-	μJ
Total Gate Charge	Q_g	$V_{DD} = 1200\text{ V}$, $I_D = 2\text{ A}$, $V_{GS} = -5 / +20\text{ V}$	-	13	-	nC
Gate-Source Charge	Q_{gs}		-	3.5	-	
Gate-Drain Charge	Q_{gd}		-	6	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 1200\text{ V}$, $V_{GS} = -5 / +20\text{ V}$, $I_D = 2\text{ A}$, $R_{G,ext} = 2\text{ }\Omega$, $R_L = 600\text{ }\Omega$, Timing relative to V_{DS}	-	8	-	ns
Rise Time	t_r		-	12	-	
Turn-Off Delay Time	$t_{d(off)}$		-	23	-	
Fall Time	t_f		-	74	-	

4. Reverse Diode Characteristics

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Diode Forward Voltage	V_{SD}	$I_S = 1\text{ A}$, $V_{GS} = 0\text{ V}$	-	3.7	-	V
		$I_S = 1\text{ A}$, $V_{GS} = 0\text{ V}$, $T_J = 175\text{ }^{\circ}\text{C}$	-	3.2	-	
Continuous Diode Forward Current	I_S	$V_{GS} = 0\text{ V}$, $T_C = 25\text{ }^{\circ}\text{C}$	-	-	9	A
Peak Diode Forward Current ¹	I_{SP}		-	-	15	

Footnote 1: Pulse width limited by $T_{J,MAX}$

5. Figure Data

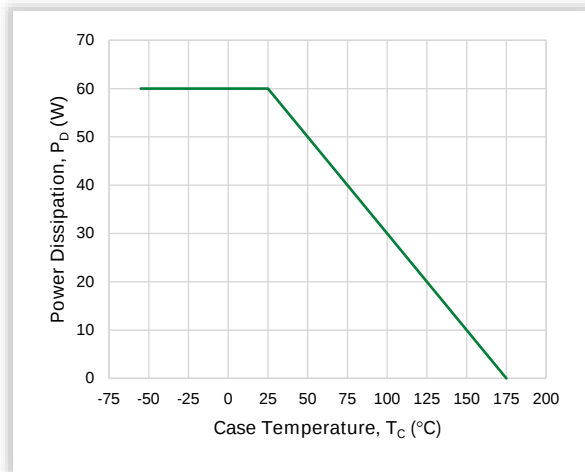
Figure 1. Maximum Power Dissipation ($T_J = 175^\circ\text{C}$)

Figure 2. Typical Transfer Characteristics

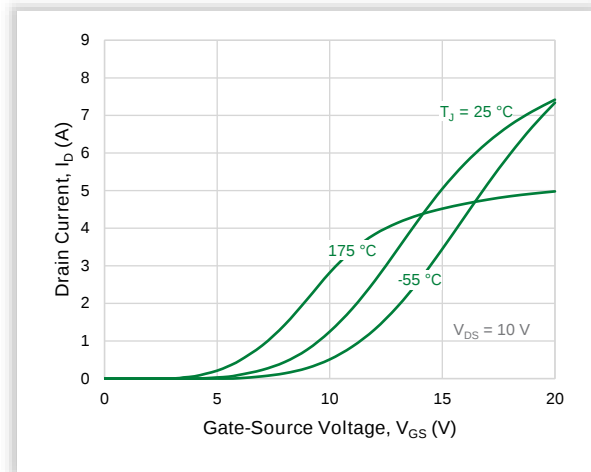
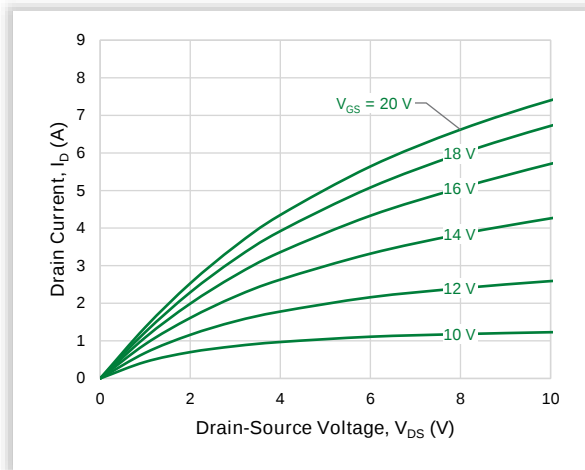
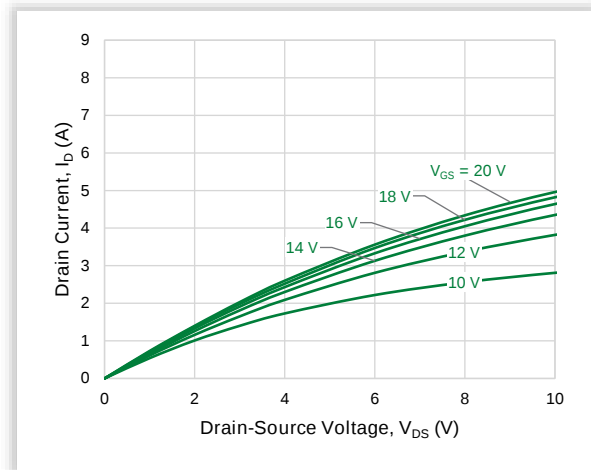
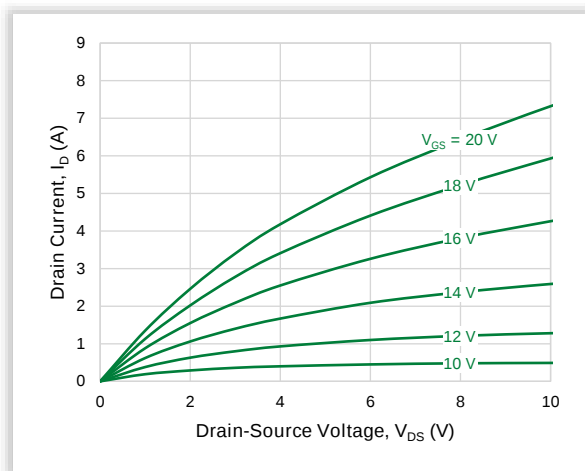
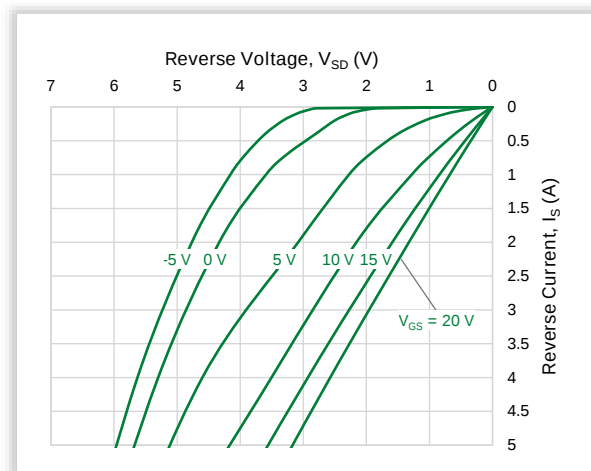
Figure 3. Typical Output Characteristics ($T_J = 25^\circ\text{C}$)Figure 4. Typical Output Characteristics ($T_J = 175^\circ\text{C}$)Figure 5. Typical Output Characteristics ($T_J = -55^\circ\text{C}$)Figure 6. Typical Reverse Conduction Characteristics ($T_J = 25^\circ\text{C}$)

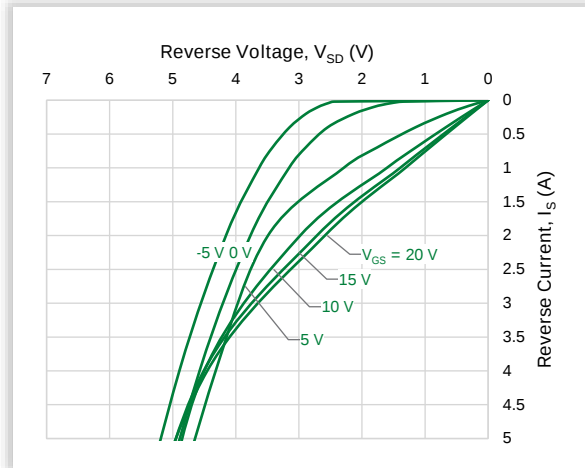
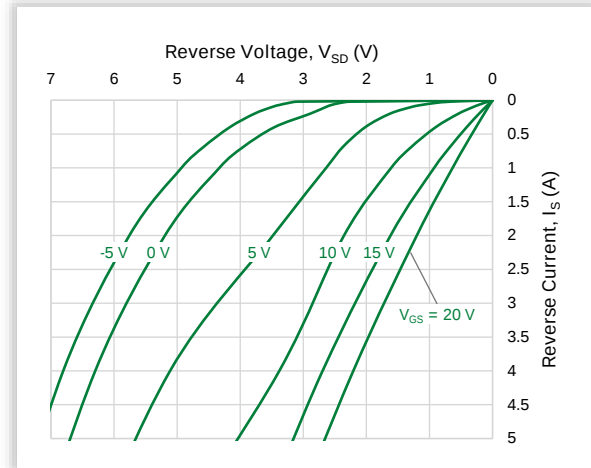
Figure 7. Typical Reverse Conduction Characteristics ($T_J = 175^\circ\text{C}$)

Figure 8. Typical Reverse Conduction Characteristics ($T_J = -55^\circ\text{C}$)


Figure 9. Transient Thermal Impedance

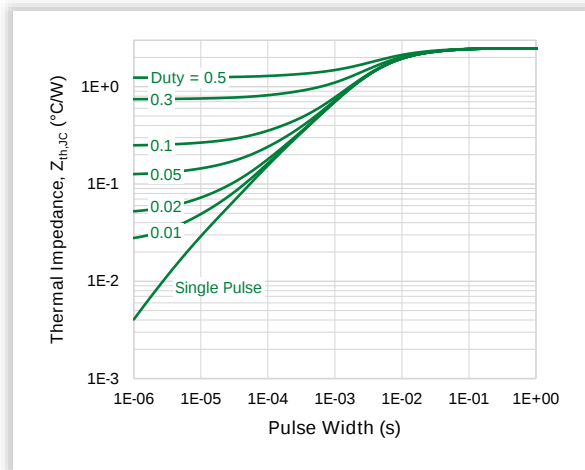
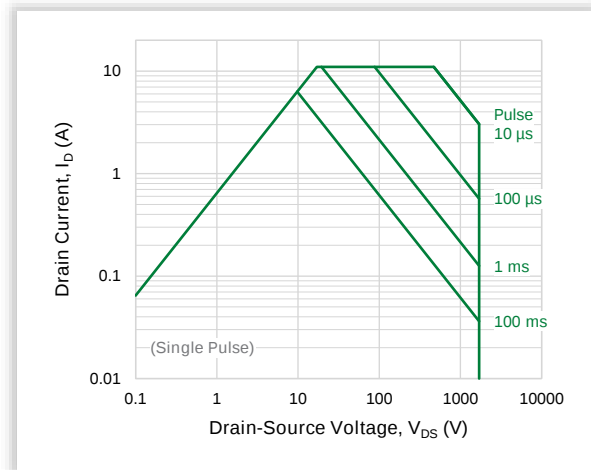

Figure 10. Maximum Safe Operating Area ($T_C = 25^\circ\text{C}$)


Figure 11. Typical On-resistance vs. Drain Current

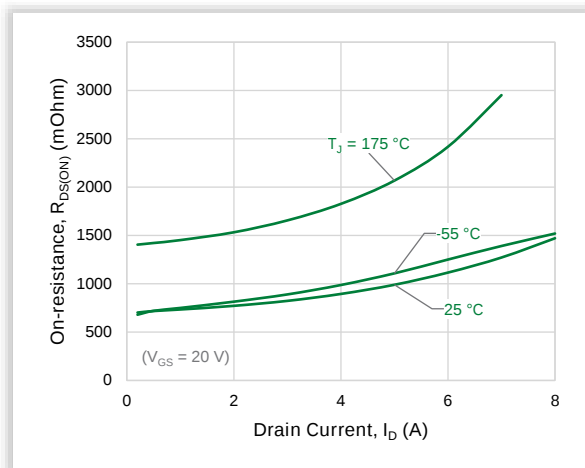


Figure 12. Normalized On-resistance vs. Junction Temperature

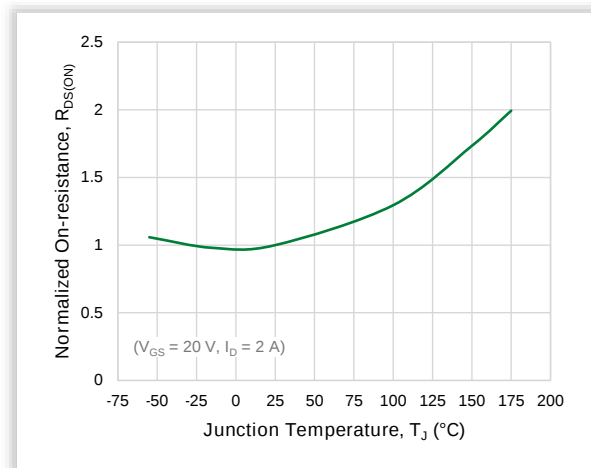


Figure 13. Typical On-resistance vs. Junction Temperature

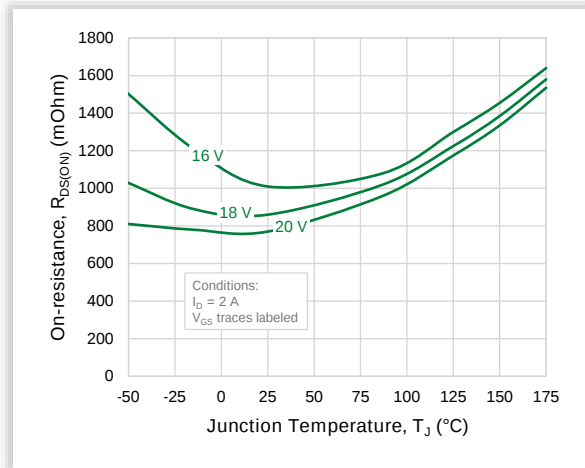


Figure 14. Typical Threshold Voltage

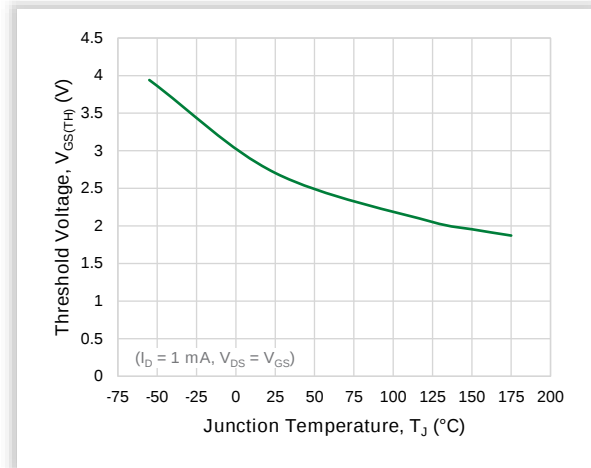


Figure 15. Typical Junction Capacitances up to 1000 V

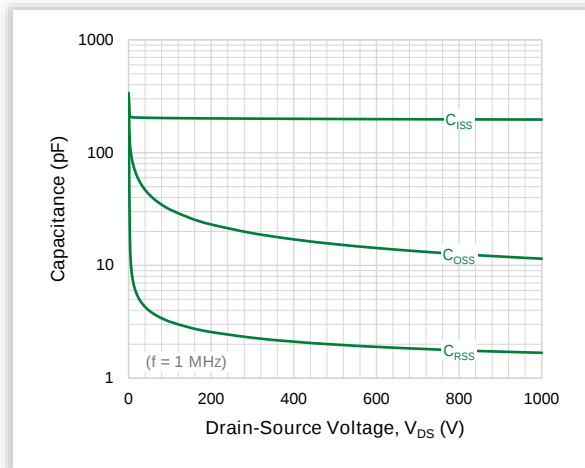


Figure 16. Typical Junction Capacitances up to 200 V

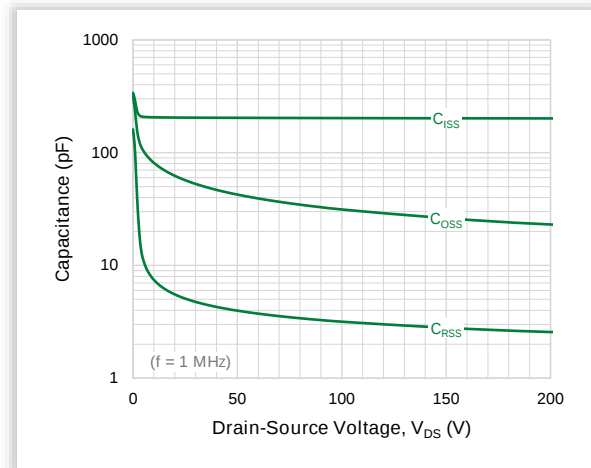


Figure 17. Typical C_OSS Stored Energy E_OSS

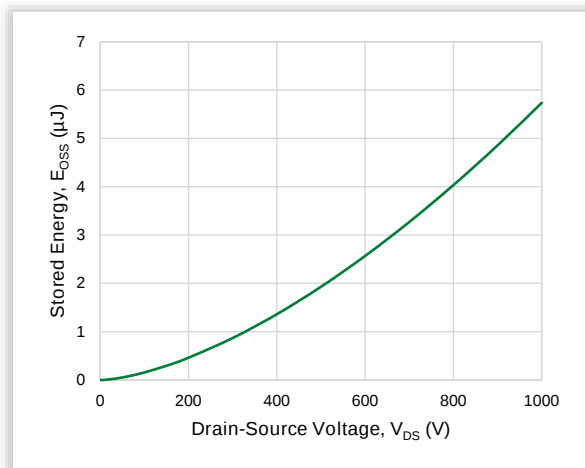


Figure 18. Typical Gate Charge

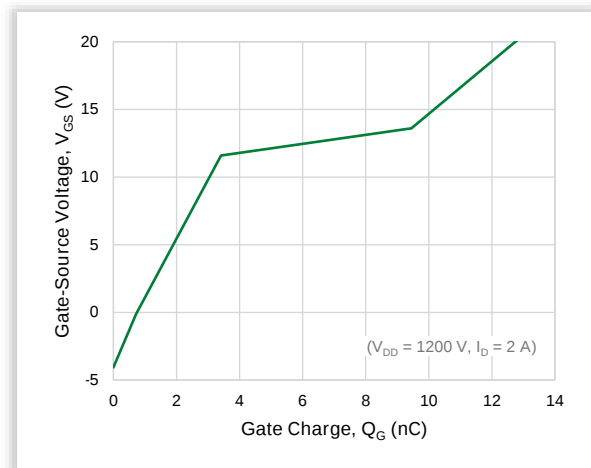


Figure 19. Typical Switching Energy vs. Drain Current

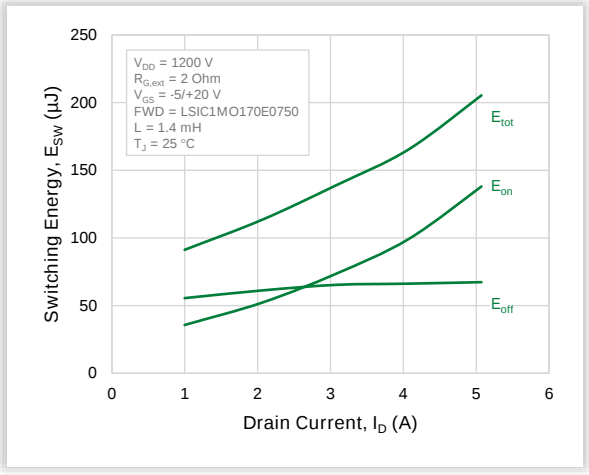


Figure 20. Typical Switching Energy vs. External Gate Resistance

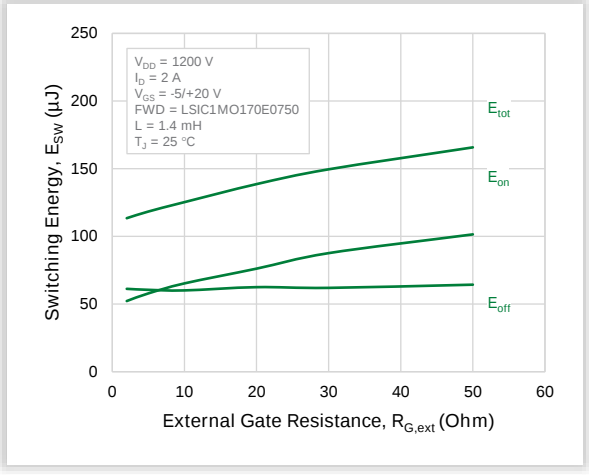
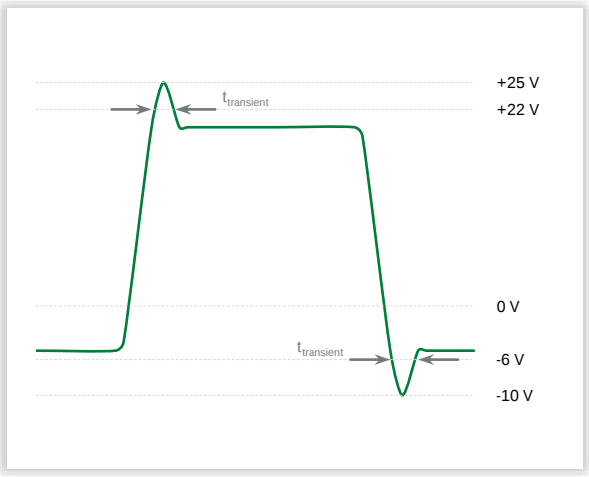
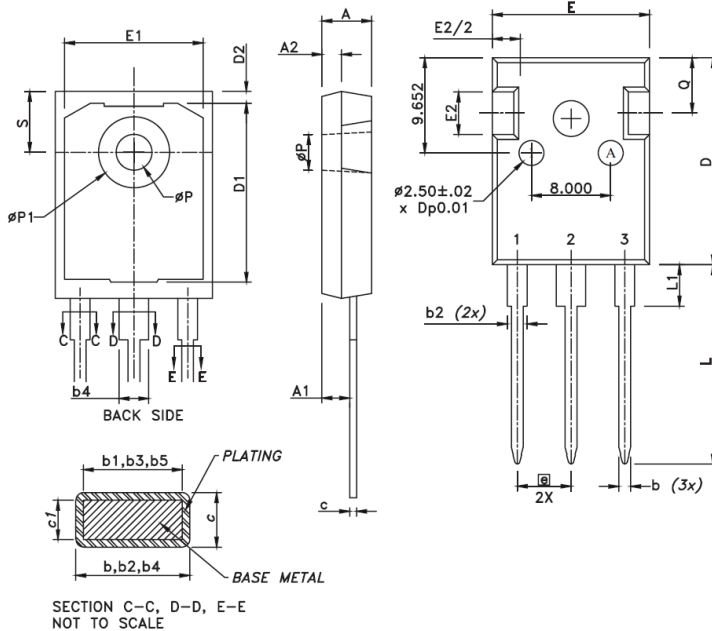


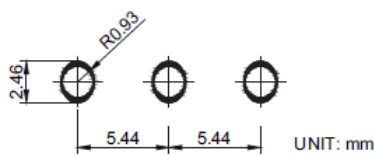
Figure 21. V_{GS} Waveform Definitions



6. Package Dimensions



Recommended Hole Pattern Layout:

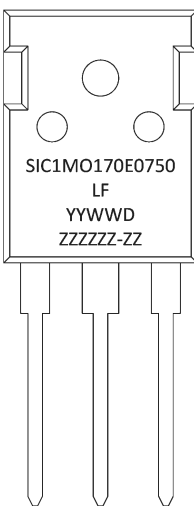


Notes:

1. Dimensions are in millimeters
2. Dimensions D & E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extreme of the plastic body.
3. ϕP to have a maximum draft angle of 1.7° to the top of the part with a maximum hole diameter of 3.912 mm.

Symbol	Millimeters		
	Min	Nom	Max
A	4.699	-	5.309
A1	2.210	-	2.591
A2	1.499	-	2.489
b	0.990	-	1.400
b2	1.650	-	2.390
b4	2.590	-	3.430
c	0.380	-	0.890
D	20.800	-	21.463
D1	13.081	-	-
D2	0.508	-	1.350
e	5.440 BSC		
E	15.494	-	16.256
E1	13.060	-	14.150
E2	3.429	-	5.486
L	19.810	-	20.570
L1	3.810	-	4.496
ϕP	3.550	-	3.660
$\phi P1$	7.060	-	7.390
Q	5.385	-	6.200
S	6.050	-	6.300

7. Part Numbering and Marking

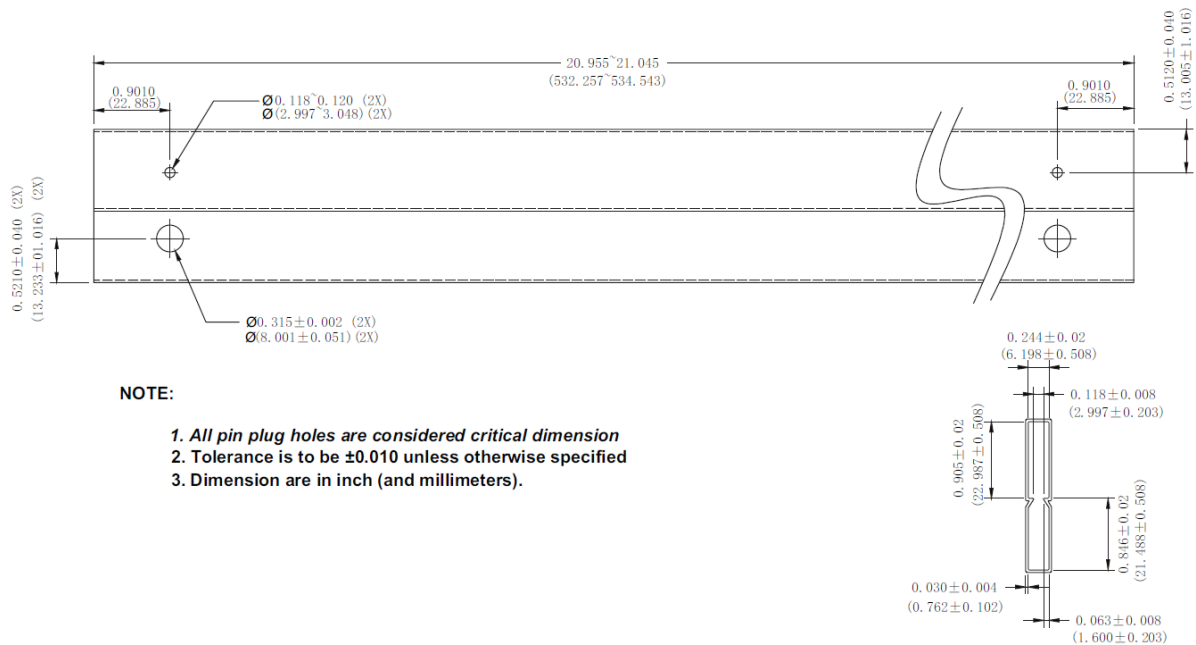


SiC	= SiC
1	= Gen 1
MO	= MOSFET
170	= Voltage Rating (1700 V)
E	= TO-247-3L
0750	= $R_{DS(ON)}$ (750 mOhm)
YY	= Year
WW	= Week
D	= Special Code
ZZZZZZ-ZZ	= Lot Number

8. Packing Options

Part Number	Marking	Packing Mode	M.O.Q.
LSIC1MO170E0750	SIC1MO170E0750	Tube (30 Pcs)	450

9. Packing Specifications



For additional information please visit www.Littelfuse.com/powersemi

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